Unit: mm

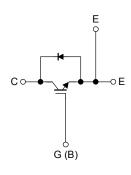
TOSHIBA IGBT Module Silicon N Channel IGBT

## MG400Q1US65H

# High Power & High Speed Switching Applications

- High input impedance
- Enhancement-mode
- The electrodes are isolated from case.

#### **Equivalent Circuit**



#### **Maximum Ratings (Ta = 25°C)**

\$ 50,000 C C C C C C C C C C C C C C C C C	2-M4  2-M6  4-96.6±0.3  80 00 00 00 00 00 00 00 00 00 00 00 00 0
- 28-5	6±0.5 22.5±0.6 22.5±0.6 54±0.6 22.5±0.6 22.5±0.6 54±0.6
JEDEC	_
JEITA	_
TOSHIBA	2-109F1A

Weight: 465 g (typ.)

Characteri	stics	Symbol	Rating	Unit	
Collector-emitter volta	ge	V <sub>CES</sub>	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ic	400	Α	
	1 ms	I <sub>CP</sub>	800		
	DC	I <sub>F</sub>	400	Α	
Forward current	1 ms	I <sub>FM</sub>	800		
Collector power dissip (Tc = 25°C)	ation	P <sub>C</sub>	2650	W	
Junction temperature		Tj	150	°C	
Storage temperature r	ange	T <sub>stg</sub>	-40 to 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 minute)	V	
Screw torque	Terminal	_	3	N·m	
Sciew torque	Mounting	_	3		

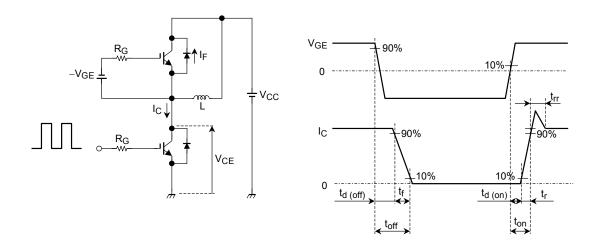
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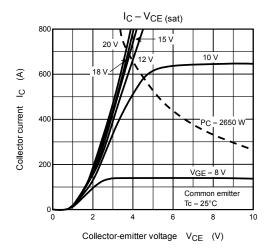


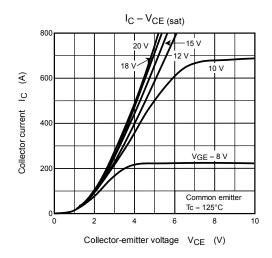
### **Electrical Characteristics (Ta = 25°C)**

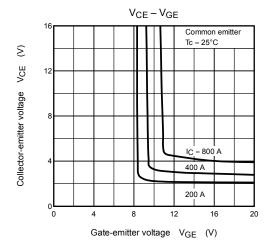
Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$		_	_	±500	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 1200 V, V <sub>GE</sub> = 0			_	4.0	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	$I_C = 400 \text{ mA}, V_{CE} = 5 \text{ V}$		4.0	_	7.0	V
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 400 A, V <sub>GE</sub> = 15 V	Tc = 25°C		3.0	4.0	· v
				Tc = 125°C		3.6		
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz			34000	_	pF
Switching time	Turn-on delay time	t <sub>d (on)</sub>			0.05		μs	
	Rise time	t <sub>r</sub>	Inductive load $V_{CC}=600~\text{V, I}_{C}=400~\text{A}$ $V_{GE}=\pm15~\text{V, R}_{G}=2.4~\Omega$			0.05		_
	Turn-on time	t <sub>on</sub>				0.10		_
	Turn-off delay time	t <sub>d (off)</sub>			_	0.55		_
	Fall time	t <sub>f</sub>				0.05		0.15
	Turn-off time	t <sub>off</sub>				0.60		_
Forward voltage		V <sub>F</sub>	$I_F = 400 \text{ A}, V_{GE} = 0$		_	2.4	3.5	V
Reverse recovery time		t <sub>rr</sub>	$I_F = 400 \text{ A}, V_{GE} = -10 \text{ V}$			0.25	_	μS
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage			_	0.047	°C/W
			Diode stage			_	0.1	
Switching loss	Turn-on	E <sub>on</sub>	Inductive load $\begin{array}{l} \text{Inductive load} \\ \text{V}_{CC} = 600 \text{ V, I}_{C} = 400 \text{ A} \\ \text{V}_{GE} = \pm 15 \text{ V, R}_{G} = 2.4 \Omega \\ \text{Tc} = 125^{\circ}\text{C} \end{array}$			40	_	- mJ
	Turn-off	E <sub>off</sub>				40		

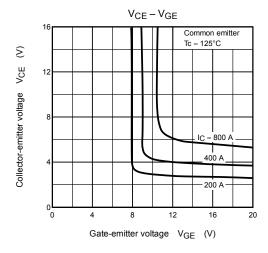
Note: Switching time measurement circuit and input/output waveforms

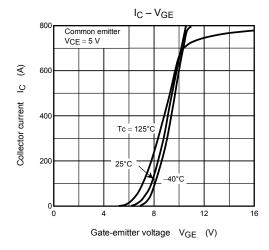


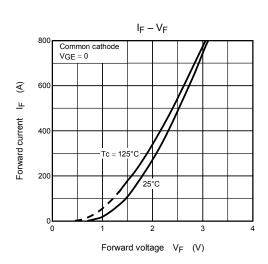


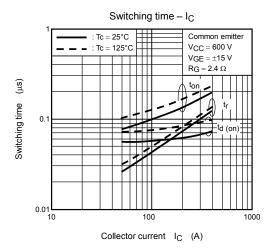


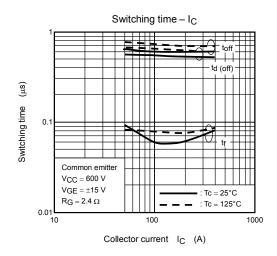


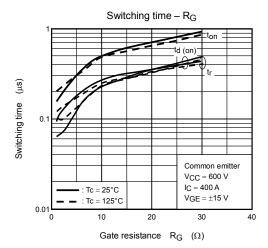


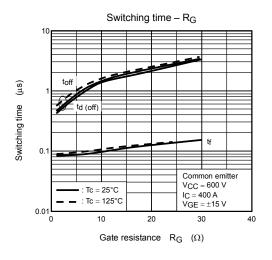


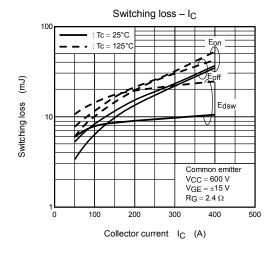


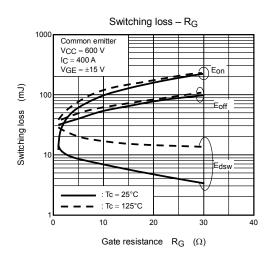


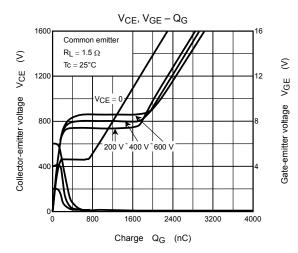


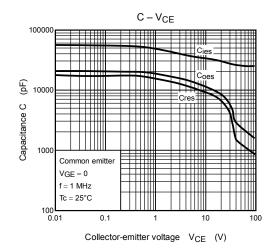


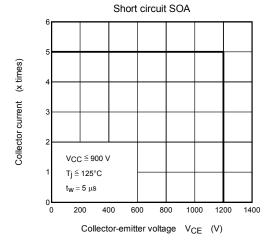


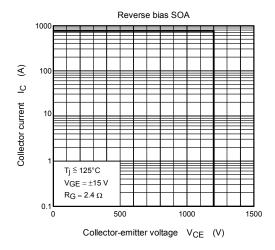


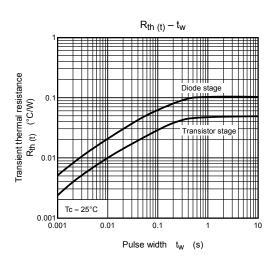












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